

5 ABSTRACT OF THE DISCLOSURE

10 An EL element and an interface between a channel and an
impurity diffusion area of a thin film transistor provided in the
vicinity of the EL element are spaced apart. A light shielding
film is provided between the EL element and the interface. By
15 providing such a space and/or the light shielding film,
generation of a leak current, which would otherwise be caused by
light emitted from the self-emissive EL element entering the TFT,
is reliably prevented, thereby ensuring that emitted light is not
brighter than a predetermined luminance.

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